

Description

The BSH111BKR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



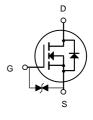
SOT-23

General Features

 $V_{DS} = 60V I_{D} = 0.3A$

 $R_{DS(ON)} < 2\Omega$ @ $V_{GS}=10V$

ESD Rating: HBM≥2000V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
BSH111BKR	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
Vos	Drain-Source Voltage		60	V
V _G S	Gate-Source Voltage	±20	V	
		T _A =25℃	0.3	
I _D	Continuous Drain Current (TJ =150°C)	T _A =100°C	0.19	A
Ідм	Drain Current-Pulsed (Note 1)		0.8	А
P _D	Maximum Power Dissipation	0.35	W	
TJ,Tstg	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (350	°C/W	



Electrical Characteristics (T_A=25 ℃unless otherwise noted)

Parameter Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60	68	-	V
Zero Gate Voltage Drain Current	loss	V_{DS} =60V, V_{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±10V,V _{DS} =0V	-	±100	±500	nA
		V _{GS} =±20V,V _{DS} =0V	-	±4	±10	uA
Gate Threshold Voltage	VGS(th)	V_{DS} = V_{GS} , I_D =250 μ A	0.7	1.2	1.9	V
		V_{GS} =5V, I_D =0.1A	-	1.3	3	Ω
Drain-Source On-State Resistance	Rds(on)	V _{GS} =10V, I _D =0.1A	-	1	2	Ω
Forward Transconductance	g FS	V _{DS} =10V,I _D =0.2A	0.1	-	-	S
Input Capacitance	C _{lss}		-	21	50	PF
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	-	11	25	PF
Reverse Transfer Capacitance	C _{rss}	1 – 1.01411 12	-	4.2	5	PF
Turn-on Delay Time	td(on)		-	10	-	nS
Turn-on Rise Time	t _r	V _{DD} =30V,I _D =0.2A	-	50	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =10V, R_{GEN} =10 Ω	-	17	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
		V _{DS} =10V,I _D =0.3A,				
Total Gate Charge	Q_g	V _{GS} =4.5V	-	1.7	3	nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	0.3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical And Thermal Characteristics

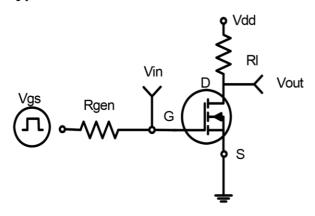


Figure 1:Switching Test Circuit

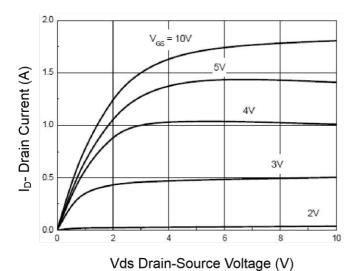


Figure 3 Output Characteristics

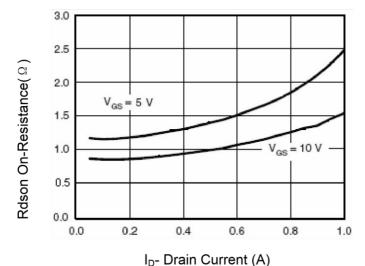


Figure 5 Drain-Source On-Resistance

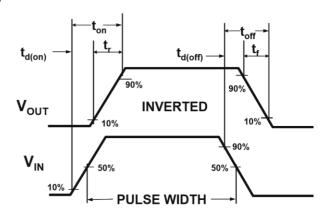


Figure 2:Switching Waveforms

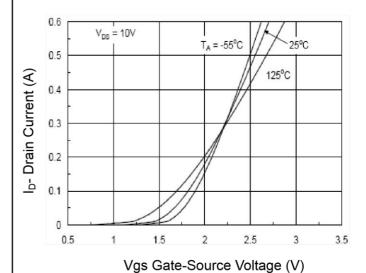
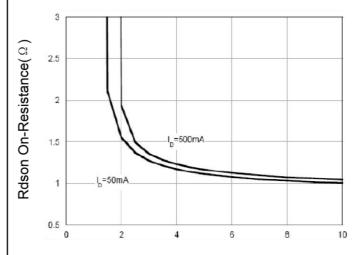
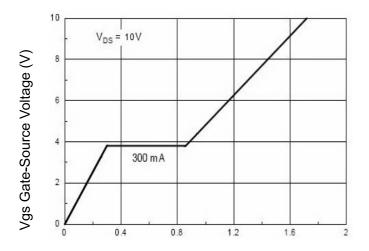


Figure 4 Transfer Characteristics

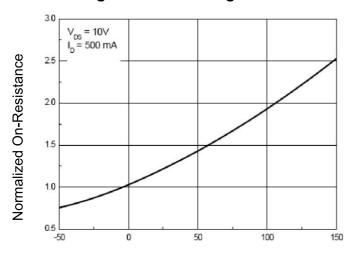


Vgs Gate-Source Voltage (V)
Figure 6 Rdson vs Vgs





Qg Gate Charge (nC) Figure 7 Gate Charge



 T_J -Junction Temperature(${}^{\circ}C$)
Figure 9 Drain-Source On-Resistance

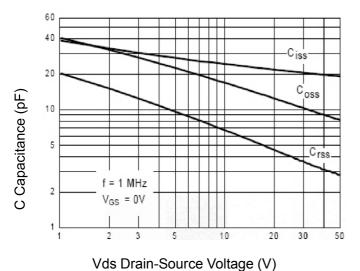
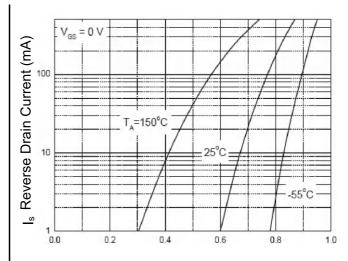
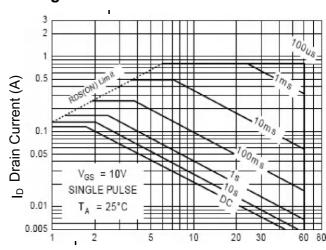


Figure 11 Capacitance vs Vds



Vsd Source-Drain Voltage (V)
Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V)
Figure 10 Safe Operation Area



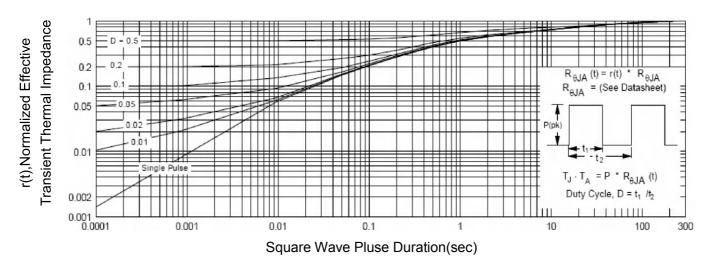
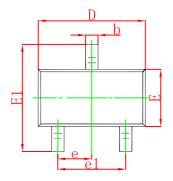
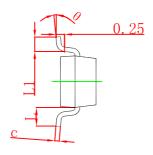


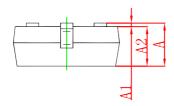
Figure 12 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

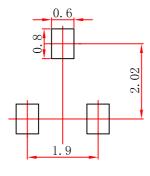






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0 TYP 0.037 TYP		7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550	REF	0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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